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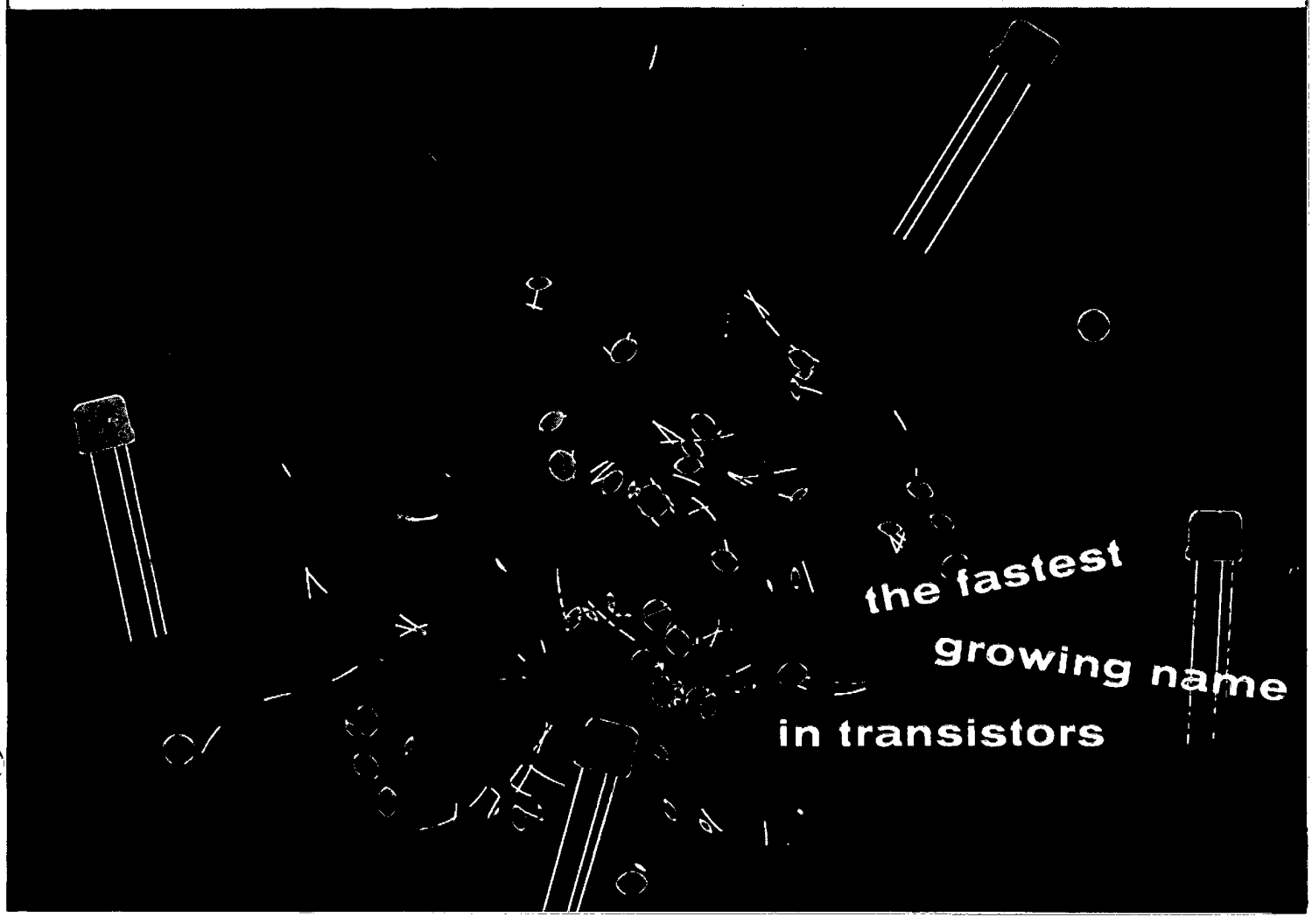
R-144A

GENERAL TRANSISTOR



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DIFFUSED P-N-P JUNCTION TRANSISTORS

Recognized for fine quality, dependability and capable service — no wonder General Transistor is rapidly becoming one of the largest manufacturers of transistors in the world.

★ Audio transistors ★ Switching circuit transistors ★ Sub-miniature hearing aid transistors
★ High frequency and computer transistors ★ Low noise audio transistors
★ High voltage switching transistors ★ Symmetrical transistors ★ Phototransistors

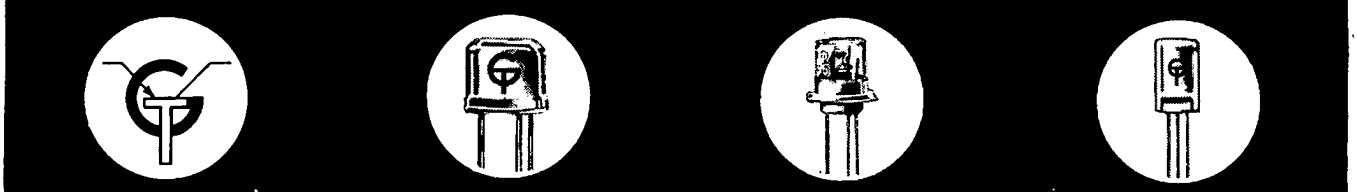
General Transistor Corp. Type	Maximum Ratings		Typical Operation						Application
	Collector Volts	Collector Dissipation (@ 25°C.) mw	Collector Cutoff Current μA (max.)	Collector Volts	Emitter Current mA	Power Gain db	Base Current Ampli. Factor β	Noise Figure db	
GT-222	−12	125	20	−4.5	−1	30	20	30	Audio
GT-14(2N63)	−25	125	10	−4.5	−1	36	28	16	Audio
GT-20(2N64)	−25	125	10	−4.5	−1	40	45	16	Audio
GT-34	−25	125	10	−4.5	−1	32	15	16	Audio
GT-81(2N65)	−25	125	10	−4.5	−1	42	90	16	Audio
GT-109	−25	125	10	−4.5	−1	42	90	16	Audio, matched pair
2N43	−45	150	10	−4.5	−1	40	40	16	Audio
2N44	−45	150	10	−4.5	−1	36	24	16	Audio
2N45	−45	150	10	−4.5	−1	33	20	16	Audio
GT-14H	−12	90	10	−4.5	−1	36	28	12	Sub-min., hearing aid
GT-20H	−12	90	10	−4.5	−1	40	45	12	Sub-min., hearing aid
GT-24H	−12	90	10	−4.5	−1	35	30	12	Sub-min., hearing aid
GT-81H	−12	90	10	−4.5	−1	42	90	12	Sub-min., hearing aid
GT-66	−12	90	10	−4.5	−1	42	100	20	Phototransistor

Maximum junction temperature: 85°C.

General Transistor Corp. Type	Maximum Ratings		Typical Operation								Application
	Collector Volts	Collector Dissipation (@ 25°C.) mw	Collector Cutoff Current (max.) μA	Emitter Cutoff Current (max.) μA	Collector Volts	Emitter Current mA	Power Gain db	Base Current Ampli. Factor β	Fα mc	Noise Figure db	
GT-83	−25	125	10	10	−4.5	−1	40	45	0.7	16	Switching-computer
GT-87	−25	125	10	10	−4.5	−1	36	38	0.5	16	Switching-computer
GT-88	−25	125	10	10	−4.5	−1	42	80	1	16	Switching-computer
GT-122	−25	125	10	10	−4.5	−1	42	80	1.5	16	Switching-computer
GT-759(2N111)	−20	90	1	5	−4.5	−1	24*	20	2.5	16	Hi-freq., computer, & IF
GT-760(2N112)	−15	90	1	5	−4.5	−1	28*	40	5	16	Hi-freq., computer, & IF
GT-761(2N113)	−12	90	1	5	−4.5	−1	32*	75	10	16	Hi-freq., computer, & RF
GT-762(2N114)	−6	90	1	5	−4.5	−1	34*	100	20	16	Hi-freq., computer, & RF
GT-763	−6	90	1	5	−4.5	−1	35*	120	30	16	Hi-freq., computer, & RF
GT-34S	−25	100	10	10	−4.5	−1	32	15		16	Symmetrical, switching, computer
GT-34HV	−50	125	10	10	−4.5	−1	32	15		16	High voltage, neon light switching

Maximum junction temperature: 85°C. *@ 455 kc

Transistor Kit No. 1 (Audio kit) Contains 1 ea. GT-14, GT-20, GT-34, GT-81, GT-83, GT-87, GT-88
Transistor Kit No. 2 (Radio kit) Contains 1—GT-761 (converter-oscillator), 2—GT-760 (intermediate frequency), 1—GT-81 (driver), 2—GT-109 (audio)
Transistor Kit No. 3 (Computer kit) Contains 1 ea. GT-122, GT-759, GT-760, GT-761, GT-762, GT-34S, GT-34HV



GENERAL TRANSISTOR CORP.

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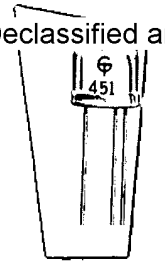
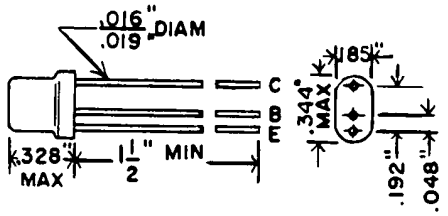


TENTATIVE SPECIFICATION BULLETIN

GENERAL TRANSISTOR CORPORATION

No. GT-760 Series

GERMANIUM PNP ALLOYED JUNCTION TRANSISTOR



APPLICATION

This series of transistors has been designed for high frequency operation as R.F. and I.F. amplifiers in broadcast receivers and as switches for high speed computer applications.

RECOMMENDED MAXIMUM RATINGS

Collector voltage	see below
Collector current	50 mw
Collector dissipation	
Junction temperature	75° C

MECHANICAL SPECIFICATIONS: Hermetically sealed in metal case with glass header.

AVERAGE CHARACTERISTICS (AT 25° C) → NEW!

		GT760	GT761	GT762	GT763
Cut-off current (I_{co}) @ 4.5 v		1 μa	1 μa	1 μa	1 μa
Extrinsic base resistance (R_b')		75	90	110	130
Collector capacitance (C_c)	@ V_c = 4.5	14 mmf	14 mmf	14 mmf	14 mmf
Alpha cut-off frequency (f_{co})	@ V_c = 4.5	5 mc	10 mc	20 mc	30 mc
L.F. current ampl. factor (α_{cb})	@ V_c = 4.5	40	70	150	200
Maximum collector voltage		15	15	6	6

TYPICAL OPERATION (455 KC)

	GT760	GT761	GT762	GT763
* Collector voltage	4.5	4.5	4.5	4.5
Collector current	1	1	1	1
** Input resistance	500	500	500	500
** Output resistance	20 K	20 K	20 K	20 K
** Power gain	31 db	33 db	34 db	34 db

* Higher gain may be realized at higher voltages since C_c drops and f_{co} and α_{cb} increase with collector voltage.

** Neutralized

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SPECIFICATION BULLETIN

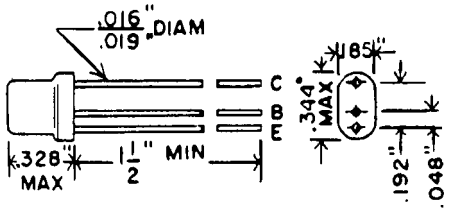
GENERAL TRANSISTOR CORPORATION

TYPE GT-109

GERMANIUM P-N-P ALLOYED JUNCTION TRANSISTOR

APPLICATION:

The General Transistor Type GT-109 germanium P-N-P alloyed junction transistor is designed primarily for use in low frequency push-pull stages such as audio amplifiers, portable radio receiver output stages and low frequency r-f amplifiers. High efficiency and low battery drain are features of its use in class B circuitry.



FEATURES:

Hermetically sealed in metal case with glass headers. Tinned flexible leads may be soldered directly into the circuit or used with standard plug-in sockets. Can be mounted in any position.

ELECTRICAL DATA:

MAXIMUM RATINGS:

Collector Voltage	—25 volts
Collector Current	(limited by dissipation)
Collector Dissipation (at 25°C)	125 mw
	200 mw (with heat sink)
Ambient Temperature	55°C

AVERAGE CHARACTERISTICS (at 25°C):

Collector Voltage	—4.5 volts
Emitter Current	—1 ma
Collector Resistance	2 meg.
Base Resistance	1400 ohms
Emitter Resistance	25 ohms
Base Current Amplification Factor	120
Cut-off Current (approx.)	6 μa

AVERAGE CHARACTERISTICS (at 25°C) PUSH-PULL PAIR:

Collector Voltage	—9 volts
Emitter Current (average)	30 ma
Input Resistance (average)	3000 ohms
Load Resistance (collector to collector)	900 ohms
Average Power Gain (matched input)	28 db
Power Output	150 mw
Percentage Distortion (average)	8%

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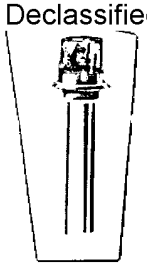

TENTATIVE SPECIFICATION BULLETIN

GENERAL TRANSISTOR CORPORATION

Type GT-66

GERMANIUM P-N-P ALLOYED JUNCTION THREE-LEAD PHOTOTRANSISTOR

APPLICATION:

The General Transistor Type GT-66 germanium P-N-P alloyed junction phototransistor is a miniature, light-sensitive photocell intended for use in circuits employing A.C. amplification for modulated light. It may also be used as a two-lead device with D.C. (unmodulated) light. In spite of its miniature size it is capable of performance at a level sufficient to operate a relay. It can be adapted to a large variety of controls. Some possible applications are: automobile headlight dimmers, tape and punch card reading, optical sound play-back, liquid level control, television receiver automatic brilliance control, industrial safety devices, automatic door openers, smoke density control, advertising displays, race timing, photoelectric rifle ranges, burglar alarms, light meters and many other ingenious applications. It is sensitive to relative position of the light source making it useful in positioning controls.

FEATURES:

The element is hermetically sealed within a glass bulb and its three leads emerge from a glass header base. The spectral response covers the visible region and extends far into the infrared. It performs the same functions as a phototube with advantages of smaller size, small power demand and high sensitivity.

Tinned flexible leads may be soldered or welded directly into the circuit (using heat sink) or used with standard plug-in sockets. It can be mounted in any position. The light source is applied to the side of the transistor, as illustrated.

ELECTRICAL DATA:

Maxium Ratings:

Collector Voltage	−12 volts
Collector Current	−20 ma
Collector Dissipation (at 25°C)	50 mw
Light Sensitivity (short circuited collector) (minimum)	25 μa/ft. Cand.
Photo Sensitive Area	(average) 1 sq. mm
Dark Current (@ −4.5 volts, open emitter)	(maximum) 15 μa
Cutoff Frequency (grounded base transistor)	(nominal) 750 kc
Equivalent Noise Illumination (1 cycle bandwith at 1000 cps; Vc=−4.5 volts)	6×10^{-5} ft. Cand.
Dynamic Source Impedance	(nominal) 20,000 ohms
Current Amplification Factor	(nominal) 100

TYPICAL OPERATION: (Modulated Light, see Circuit)

R_L=10K, R_1=20K, R_2=1K, R_3=1K

Collector Supply Voltage	−12 volts
Collector Current	− 0.5 ma
Sensitivity	0.16 volts/ft. Cand.

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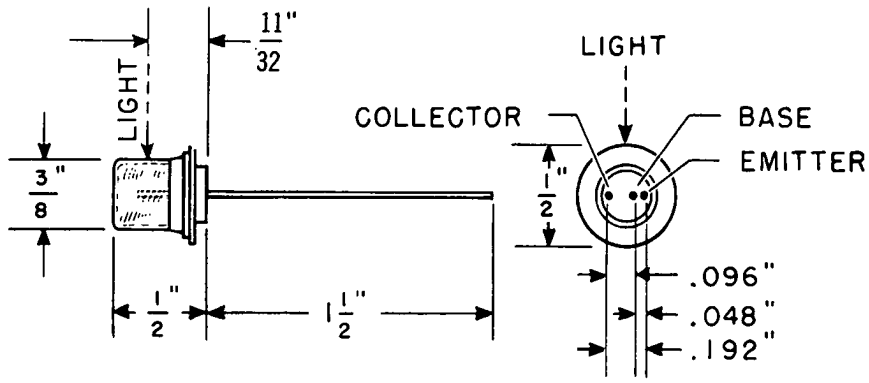
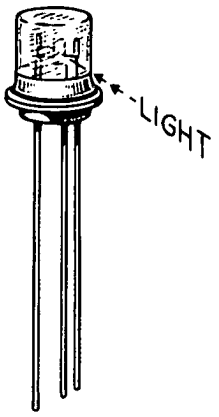
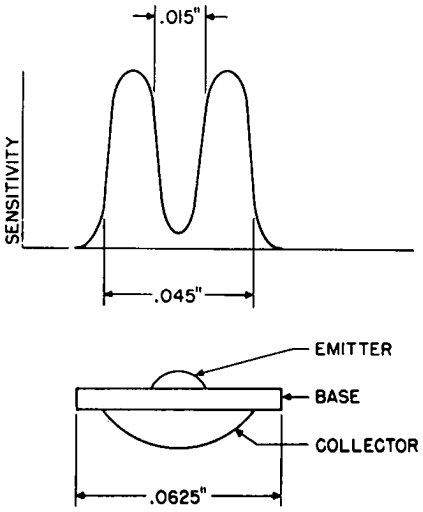
Type GT-66 GERMANIUM P-N-P PHOTOTRANSISTOR

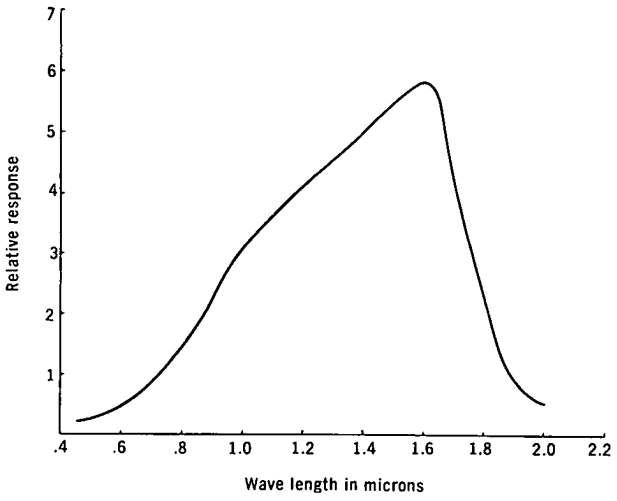


Outline Drawing

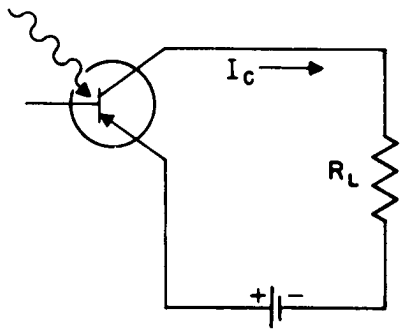




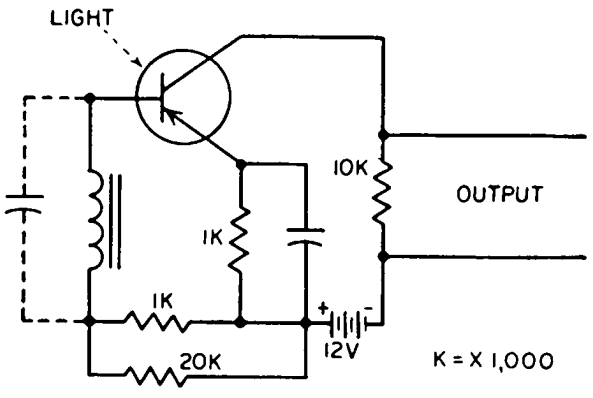
Exploration of the GT-66 photo-sensitive surface



TYPICAL SPECTRAL RESPONSE



Basic phototransistor circuit for unmodulated light



Recommended phototransistor circuit for modulated light

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SPECIFICATION BULLETIN

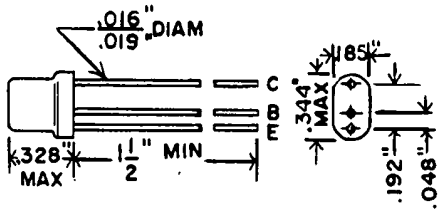
GENERAL TRANSISTOR CORPORATION

TYPE GT-34HV

GERMANIUM P-N-P ALLOYED JUNCTION TRANSISTOR

APPLICATION:

The General Transistor Type GT-34HV germanium P-N-P alloyed junction transistor is designed for high voltage applications, such as neon indicator amplifiers, computer and counter circuits, and low speed switching applications.



FEATURES:

Hermetically sealed in metal case with glass headers. Special internal wrap for greater heat dissipation. Tinned flexible leads may be soldered or welded directly into the circuit (using heat sink), or used with standard plug-in sockets. Can be mounted in any position. All units are 100% tested for design characteristics and particularly for collector-to-emitter breakdown voltage of 50 volts.

ELECTRICAL DATA:

Maximum Ratings:

Collector Voltage	−50 volts
Collector Current	(limited by dissipation)
Collector Dissipation (at 25°C)	150 mw
Ambient Temperature	50°C

Average Characteristics (at 25°C)

Collector Voltage (V_c)	−5 volts
Collector Current (I_c)	− 1 ma
Input Resistance (h_{11}) (emitter grounded)	850 ohms
(base grounded)	20 ohms
Voltage Feedback Ratio (h_{12}) (base grounded)	4×10^{-4}
Current Amplification Factor (h_{21}) (emitter grounded)	10
Collector Resistance (r_c) (minimum)	0.5 megohm
Collector Cut-off Current (maximum)	25 μa at −50 volts

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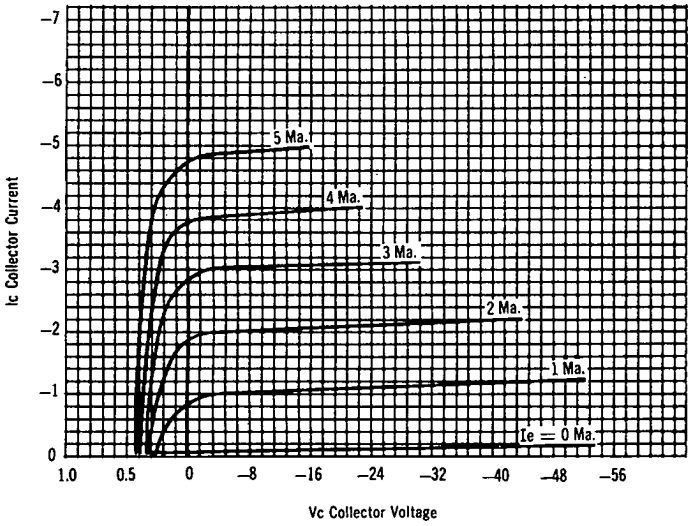
TYPE GT-34 HV

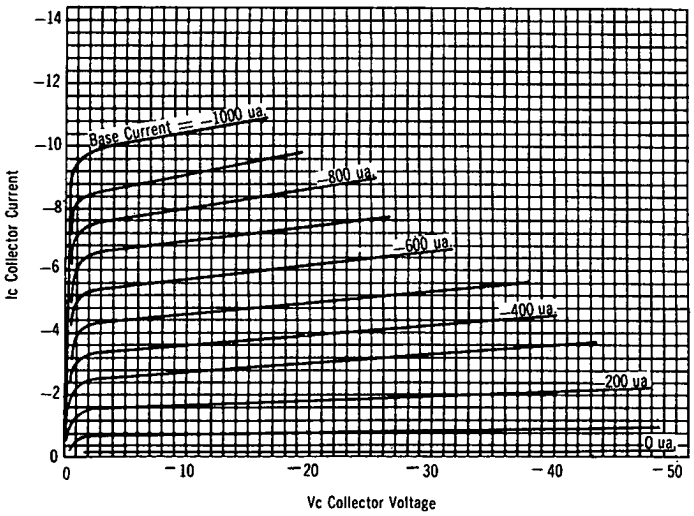
GERMANIUM P-N-P TRANSISTOR

TYPICAL CHARACTERISTICS

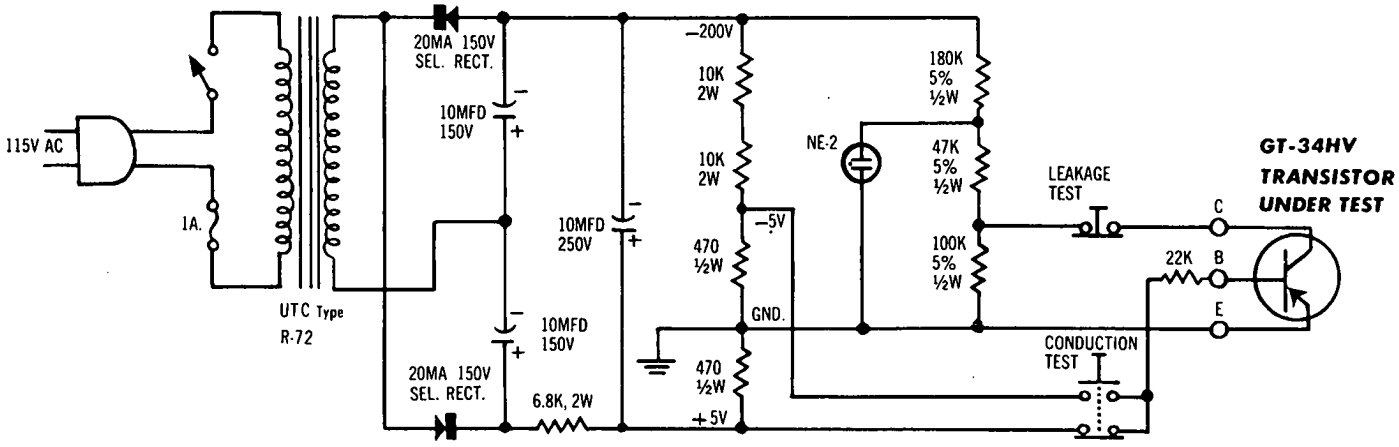
GROUNDED BASE OUTPUT CHARACTERISTICS



GROUNDED EMITTER OUTPUT CHARACTERISTICS



SUGGESTED TEST CIRCUIT



CONDUCTION TEST: Press conduction button; lamp should extinguish.

LEAKAGE TEST: Press leakage button; lamp should not increase in brilliance.

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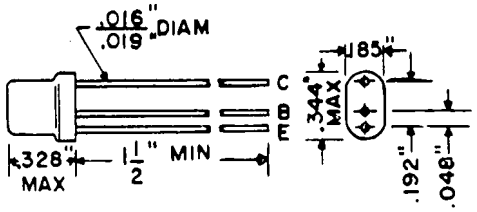
BULLETIN

TYPE GT-34S

GERMANIUM PNP BI-DIRECTIONAL TRANSISTOR



APPLICATION
This transistor has been designed for operation where bi-directional gain is required.

MECHANICAL SPECIFICATIONS: Hermetically sealed in metal case with glass header.

ABSOLUTE MAXIMUM RATINGS

		Base to Collector	Base to Emitter
Collector Voltage	Volts	−25	−25
Dissipation @ 50°C	mw	70	70
Junction Temperature	°C	85	85
Collector Cut-off Current (Vc = −15 Volts @ 25°C)	ua	15	15

AVERAGE CHARACTERISTICS @ 25° C (Collector Voltage: - 4.5 V., emitter current 1 ma, freq. 1000 cps)

			Base to Collector	Base to Emitter
Collector Resistance (r) ohms	Min.		500K	500K
	Avg.		1.5 meg.	1.5 meg.
Base Resistance (r_b) ohms	Avg.		800	800
	Max.		1500	1500
Cur. Amplification Factor (a grounded emitter)	Min.		10	10
	Avg.		15	15
	Max.		19	19
Noise Figure db	Avg.		24	24
Power Gain db	Avg.		32	32

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SPECIFICATION BULLETIN

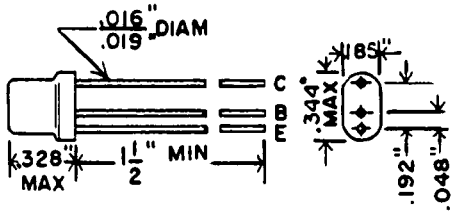
GENERAL TRANSISTOR CORPORATION

TYPE GT-88
TYPE GT-122

GERMANIUM P-N-P ALLOYED JUNCTION TRANSISTOR

APPLICATION:

These types are carefully selected and processed for reliable service in flip-flop circuits and other computer applications. The GT-88 and the GT-122 are identical except that the GT-122 is selected for a higher alpha cut-off frequency.



FEATURES:

Hermetically sealed in metal case with glass headers. Tinned flexible leads may be soldered or welded directly into the circuit (with heat sink) or used with standard plug-in sockets. Can be mounted in any postion.

ELECTRICAL DATA:

MAXIMUM RATINGS:

Collector Voltage	- 25 volts
Collector Current	(limited by dissipation)
Collector Dissipation (at 25° C)	125 mw
Junction Temperature	85° C

AVERAGE CHARACTERISTICS (at 25° C, frequency 1000 cps)

Collector Voltage	- 4.5 volts
Emitter Current	1 ma
Collector Cut-Off Current (V_c -- 4.5v)	5 ua
Current Amplification Factor (emitter grounded) GT-88	80
GT-122	100
Input Resistance (emitter grounded)	1500 ohms
Collector Resistance	1.5 megohm
Collector Capacitance (base grounded)	50 uuf
Alpha Cut-Off Frequency GT-88	1.5 mcs
GT-122	2.0 mcs
Temperature Rise per Unit Dissipation (free air)	0.4° C/mw
(infinite sink)	0.25 ° C/mw
Noise Figure	16 db

GENERAL TRANSISTOR CORP.

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P-N-P ALLOYED JUNCTION GERMANIUM TRANSISTOR

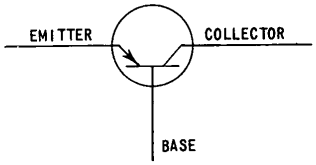
Recommended for amateurs, hobbyists, and experimenters.

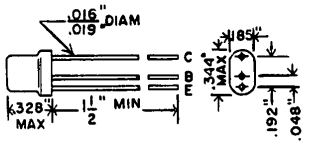
FEATURES:

Hermetically sealed in a metal case with a glass header. It can be mounted in any position. The tinned flexible leads may be soldered directly into the circuit or used with standard plug-in sockets.

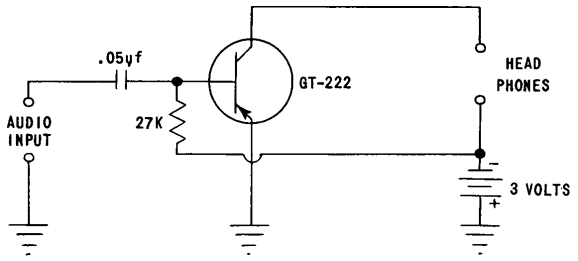
ELECTRICAL DATA:

ABSOLUTE MAXIMUM RATINGS:	
Collector Voltage	-12 volts
Collector Dissipation (at 25° C)	125 mw
Junction Temperature	85° C
AVERAGE CHARACTERISTICS:	
Collector Voltage	- 4.5 volts
Emitter Current	1 ma
Collector Resistance	1.5 megohms
Input Resistance (emitter grounded)	1000 ohms
Current Amplification Factor (emitter grounded)	20
Noise Figure	30 db
Collector Cut-Off Current	6 ua
Power Gain	30 db
TYPICAL OPERATION: (at 25° C, frequency 1000 cps, common emitter)	
Collector Voltage	- 4.5 volts
Emitter Current	1 ma
Input Impedance	800 ohms
Load Impedance	40,000 ohms
Power Gain	36 db

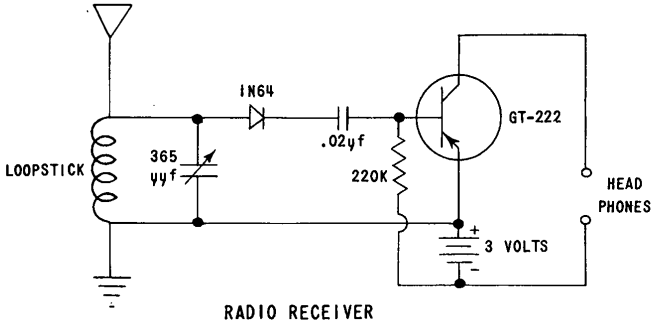




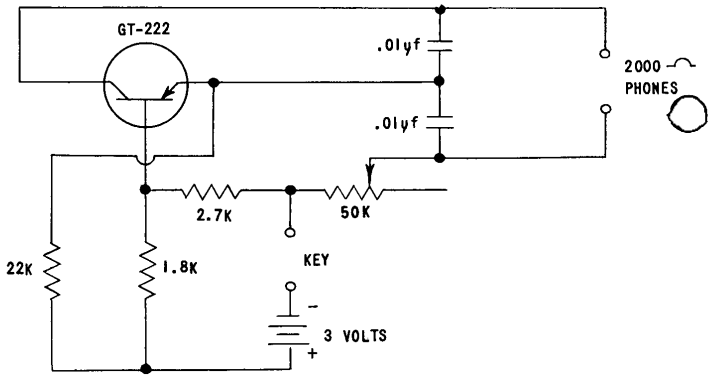
TRANSISTOR CIRCUITS



AUDIO AMPLIFIER



RADIO RECEIVER



CODE PRACTICE OSCILLATOR

GENERAL TRANSISTOR CORP.
130-11 90TH AVENUE RICHMOND HILL 18, N. Y.

NOT RECOMMENDED FOR COMMERCIAL USE
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GENERAL TRANSISTOR CORP.

GERMANIUM P-N-P ALLOYED JUNCTION TRANSISTORS

HERMETICALLY SEALED

TENTATIVE SPECIFICATIONS AND TRANSISTOR CROSS-REFERENCE SHEET

DOCUMENT NO. 2
NO CHANGE IN CLASS. ☒
☐ DECLASSIFIED
CLASS. CHANGED TO: TS S C
NEXT REVIEW DATE:
AUTH: HR 70-2
DATE: 22 JAN 1980 REVIEWER: 032100

GENERAL TRANSISTOR CORP.

Technical Bulletin No. G-7, August 1, 1956

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FOR P-N-P TYPES

	Type	Use	Maximum Junction Temp. °C	Maximum Ratings (at 25°C) Dissipat. mw	Collector Current (ma)	Collector Volts V base	Collector Volts V emitter	Characteristics[3] (at V_C=-4.5 volts, I_E=1ma, T=25°C) Beta Range	Beta Typical	Alpha Cutoff Freq. (mcs)	Comparable Reference Types* Raytheon	G E	Sylvania	R C A	C B S	T.I.	Philco	
1	GT-14	A	85	125	100	-25		20 - 34	28		CK-723, 2N63					301		1
2	GT-20	A,R	85	125	100	-25		35 - 49	42		CK-721, CK-727[1] 2N64, 2N106[1]	2N44, 2N81		2N104		301		2
3	GT-34	A	85	125	100	-25		10 - 19	15		CK-722					300		3
4	GT-81	A,R	85	125	100	-25		>50	80		CK-725, 2N65	2N43	2N34	2N77, 2N105 2N175[1]		302, 310	2N223	4
5																		5
6	GT-83	A,C	85	125	100	-25		35 - 49	42	> .7		2N76, 2N190						6
7	GT-87	A,C	85	125	100	-25		20 - 34	28	> .5		2N189						7
8	GT-88	A,C	85	125	100	-25		>50	80	> 1.0		2N191						8
9	GT-122	A,C	85	125	100	-25		>50	90	> 1.5		2N192						9
10	GT-34HV	A,C	85	125	100	-50		10 - 34	18			2N44, 2N45						10
11	GT-34S[2]	A,C,S	85	125	100	-25		>10	15		CK-870, CK-871							11
12																		12
13	GT-109[3]	A,O,R	85	125	200	-25	-12	80 - 160	120		2N138	2N186, 2N187 2N188			2N180	2N185	2N224, 2N226	13
14	GT-81HS[5]	A,O,R	85	125	200	-25	-12	80 - 160	120		CK-751				2N180			14
15																		15
16	GT-66	P	75	100 *	20	-12										800		16
17																		17
18	GT-759	A,R,C	75	100	100	-15	-6		25	3	2N111A, 2N111							18
19	GT-760	A,R,C	75	100	100	-15	-6		40	5	2N112, 2N112A CK-760	2N135		2N139				19
20	GT-761	A,R,C	75	100	100	-10	-6		70	10	CK-761, 2N113 CK-766, CK-766A	2N123, 2N136 2N137, 2N167		2N140				20
21	GT-762	A,R,C	75	100	100	-10	-6		150	20	2N114, CK-762							21
22	GT-763	A,R,C	75	100	100	-10	-6		200	30								22
23																		23
24	GT-14H	HA	75	100	50	-12		20 - 34	28		2N130				HA-1, HA-2			24
25	GT-20H	HA	75	100	50	-12		35 - 49	42		2N131, 2N133[1]				HA-3			25
26	GT-81H	HA	75	100	50	-12		>50	80		2N132						2N47, 2N49 2N62	26
27																		27
28	GT-222	A	75	125	100	-12						2N107						28

A-Audio O-Output
C-Computer R-Radio
S-Symmetrical P-Phototransistor
HA-Hearing Aid

[1] Low Noise
[2] Ratings for both reversed emitter and reversed collector
[3] Can be offered in matched pairs
[4] 40-80 at I_b=-2ma, V_c=-1 volt
[5] Supplied with Heat Sink

* This chart should be used only as a general guide. For more exact information, reference should be made to original specifications for types referred to. The General Transistor Corp. does not claim, nor does it warrant, that its transistors are exact equivalents or replacements for the types referred to.

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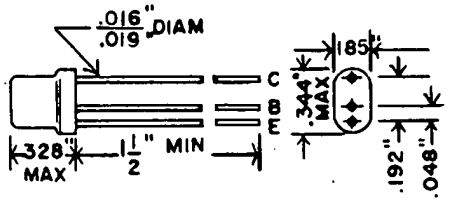
MECHANICAL SPECIFICATIONS:



AUDIO TRANSISTORS:
GT-14
GT-20
GT-34
GT-81
GT-87
GT-88

All types are available with Maximum Noise Figure of 12 db. for use in first stage of multistage amplifier. Measurement is made @1000 cps. with a 100 cps. bandwidth and is compared with the noise of a 1500 ohm input resistor. All types are available with 150 mw Max. dissipation @ 50°C for special applications.

AUDIO OUTPUT TYPES:
GT-109
GT-81HS

These germanium P-N-P alloyed junction transistors are designed primarily for use in low frequency push-pull stages such as audio amplifiers, portable radio receiver output stages and low frequency r-f amplifiers. High efficiency and low battery drain are features in class B circuitry.

HIGH FREQUENCY TYPES:
GT-759
GT-760
GT-761
GT-762
GT-763

This series of transistors has been designed for high frequency operation as R.F. and I.F. amplifiers in broadcast receivers and as switches for high speed computer applications.

LOW SPEED COMPUTER TYPES:

HIGH VOLTAGE TYPE:
GT-34HV

The General Transistor Type GT-34HV germanium P-N-P alloyed junction transistor is designed for high voltage applications, such as neon indicator amplifiers, computer and counter curcuits, and low speed switching applications.

SWITCHING TYPES:
GT-88
GT-122

These types are carefully selected and processed for reliable service in flip-flop circuits and other computer applications. The GT-88 and the GT-122 are identical except that the GT-122 is selected for a higher alpha cut-off frequency.

SYMMETRICAL TYPE:
GT-34S

This transistor has been designed for operation where bi-directional gain is required.

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